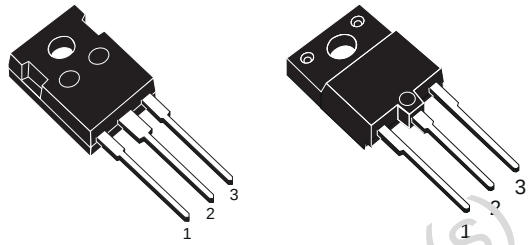
STW15NB50
STH15NB50FI

N-CHANNEL 500V - 0.33Ω - 14.6A - T0-247/ISOWATT218 PowerMESH™ MOSFET

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STW15NB50	500 V	< 0.36 Ω	14.6 A
STH15NB50FI	500 V	< 0.36 Ω	10.5 A

- TYPICAL $R_{DS(on)}$ = 0.33 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- ± 30V GATE TO SOURCE VOLTAGE RATING
- 100% AVALANCHE TESTED
- VERY LOW INTRINSIC CAPACITANCES
- GATE CHARGE MINIMIZED

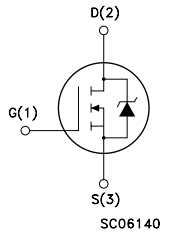


TO-247 **ISOWATT218**

DESCRIPTION

Using the latest high voltage MESH OVERLAY™ process, SGS-Thomson has designed an advanced family of power MOSFETs with outstanding performances. The new patent pending strip layout coupled with the Company's proprietary edge termination structure, gives the lowest RDS(on) per area, exceptional avalanche and dv/dt capabilities and unrivalled gate charge and switching characteristics.

INTERNAL SCHEMATIC DIAGRAM



APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVE

Obsolete Product(s) Obsolete Product(s)

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STW15NB50	STH15NB50FI	
V_{DS}	Drain-source Voltage (V_{GS} = 0)	500		V
V_{DGR}	Drain- gate Voltage (R_{GS} = 20 kΩ)	500		V
V_{GS}	Gate-source Voltage	± 30		V
I_D	Drain Current (continuous) at T_c = 25 °C	14.6	10.5	A
I_D	Drain Current (continuous) at T_c = 100 °C	9.2	6.6	A
I_{DM}(•)	Drain Current (pulsed)	58.4	58.4	A
P_{tot}	Total Dissipation at T_c = 25 °C	190	80	W
	Derating Factor	0.64	1.52	W/°C
dv/dt(1)	Peak Diode Recovery voltage slope	4		V/ns
V_{ISO}	Insulation Withstand Voltage (DC)	4000		V
T_{stg}	Storage Temperature	-65 to 150		°C
T_j	Max. Operating Junction Temperature	150		°C

THERMAL DATA

			TO-247	ISOWATT218	
$R_{thj\text{-}case}$	Thermal Resistance Junction-case	Max	0.66	1.56	°C/W
$R_{thj\text{-}amb}$	Thermal Resistance Junction-ambient	Max	30		°C/W
$R_{thc\text{-}sink}$	Thermal Resistance Case-sink	Typ	0.1		°C/W
T_l	Maximum Lead Temperature For Soldering Purpose		300		°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	14.6	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 °C, $I_D = I_{AR}$, V_{DD} = 50 V)	850	mJ

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA V_{GS} = 0	500			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating V_{DS} = Max Rating T_c = 125 °C			1 50	µA µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ± 30 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS} I_D = 250 µA	3	4	5	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10 V I_D = 7.5 A		0.33	0.36	Ω Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ V_{GS} = 10 V	14.6			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (*)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ I_D = 7.5 A	8	12		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V_{DS} = 25 V f = 1 MHz V_{GS} = 0		2600 330 40	3400 430 55	pF pF pF

Obsolete Product(s) Obsolete Product(s)

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	V_{DD} = 250 V I_D = 7.5 A R_G = 4.7 Ω V_{GS} = 10 V (see test circuit, figure 3)		24 14	34 20	ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD} = 400 V I_D = 15 A V_{GS} = 10 V		60 15 27	80	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	V_{DD} = 400 V I_D = 15 A R_G = 4.7 Ω V_{GS} = 10 V (see test circuit, figure 5)		15 25 35	20 33 47	ns ns ns

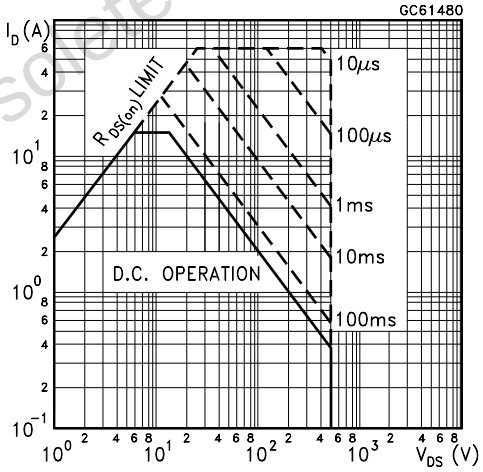
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM}(•)	Source-drain Current Source-drain Current (pulsed)				14.6 58.4	A A
V_{SD} (*)	Forward On Voltage	I_{SD} = 15 A V_{GS} = 0			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 15 A di/dt = 100 A/µs V_{DD} = 100 V T_j = 150 °C (see test circuit, figure 5)		680 9 26		ns µC A

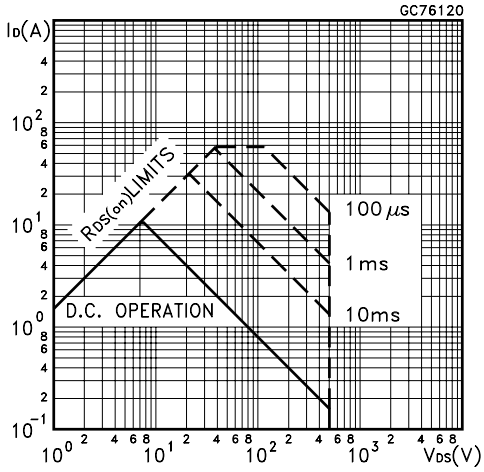
(*) Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %
(•) Pulse width limited by safe operating area

Obsolete Product(s) - Obsolete Product(s)

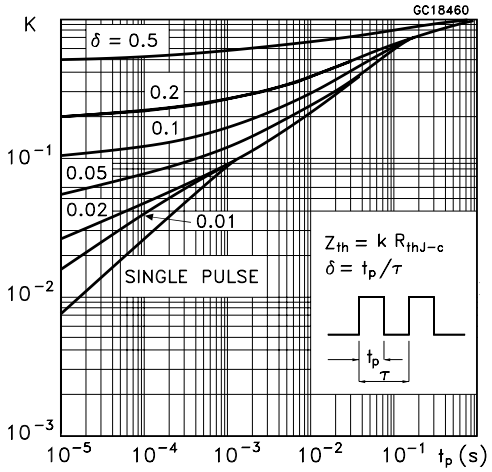
Safe Operating Area for TO-247



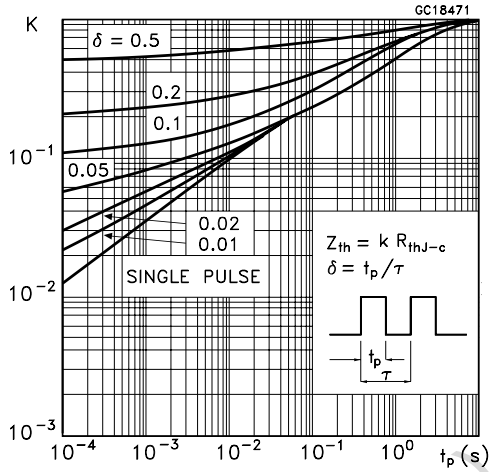
Safe Operating Area for ISOWATT218



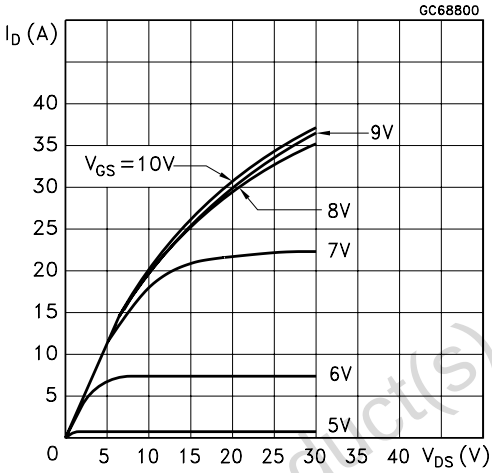
Thermal Impedance for TO-247



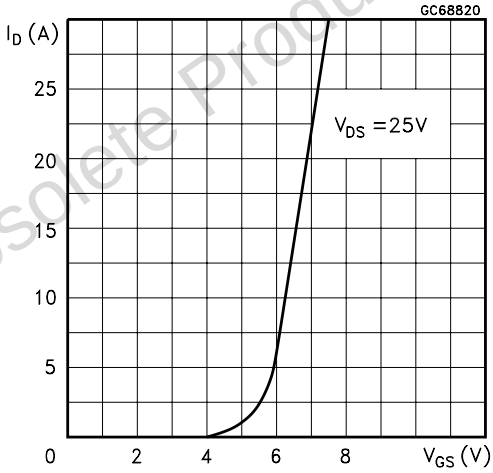
Thermal Impedance for ISOWATT218



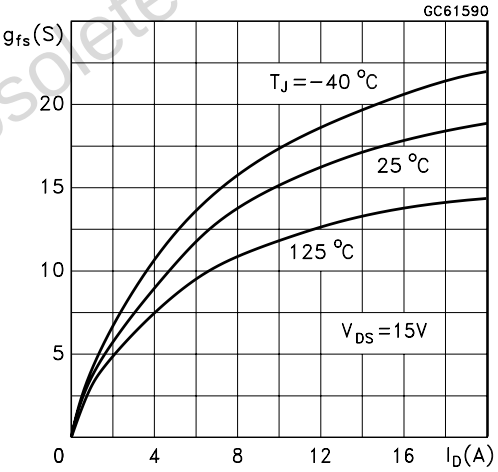
Output Characteristics



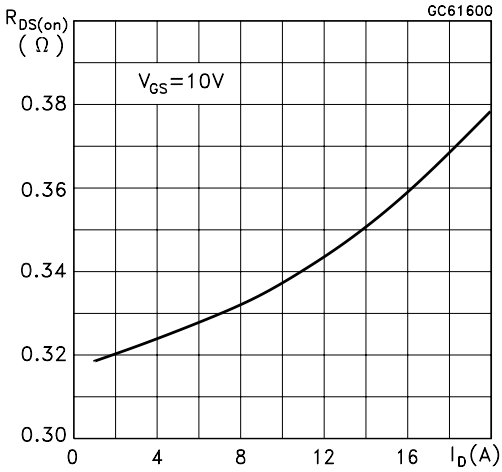
Transfer Characteristics



Transconductance

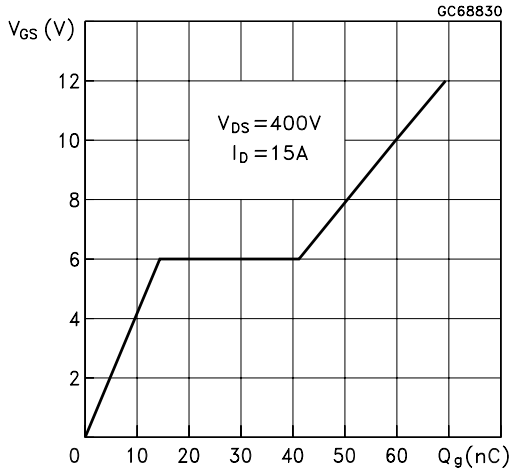


Static Drain-source On Resistance

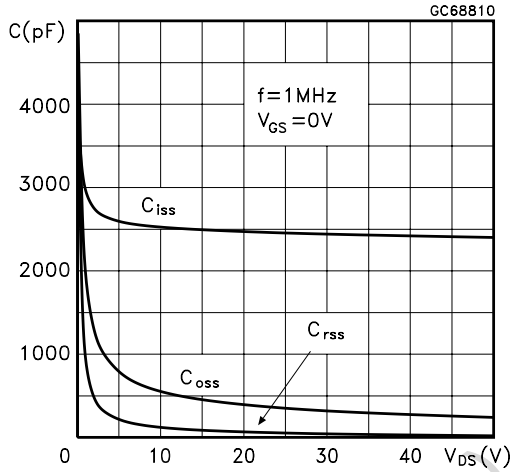


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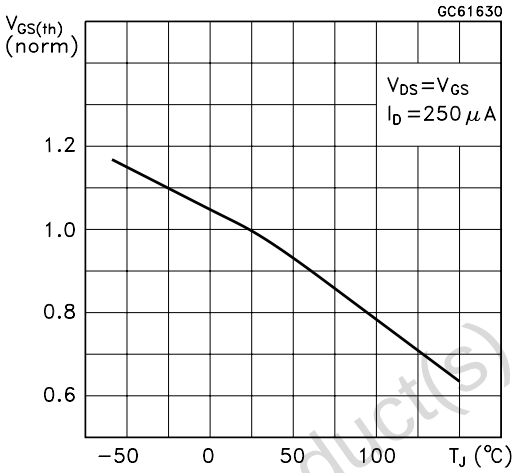
Gate Charge vs Gate-source Voltage



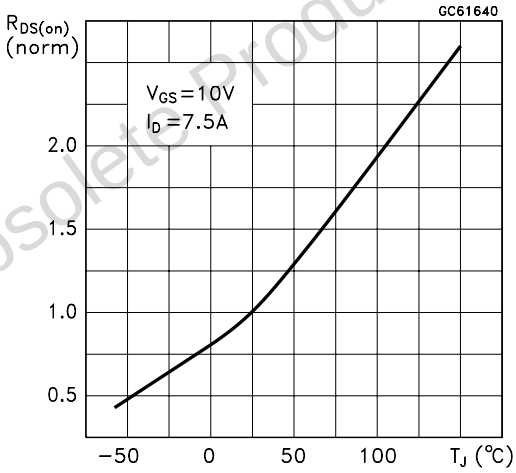
Capacitance Variations



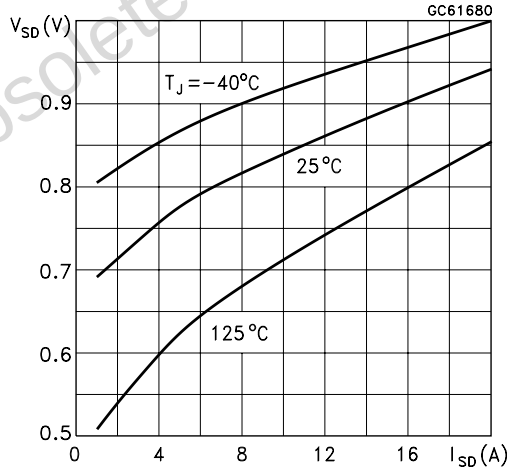
Normalized Gate Threshold Voltage vs Temperature



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics



Obsolete Product(s) - Obsolete Product(s)

Fig. 1: Unclamped Inductive Load Test Circuit

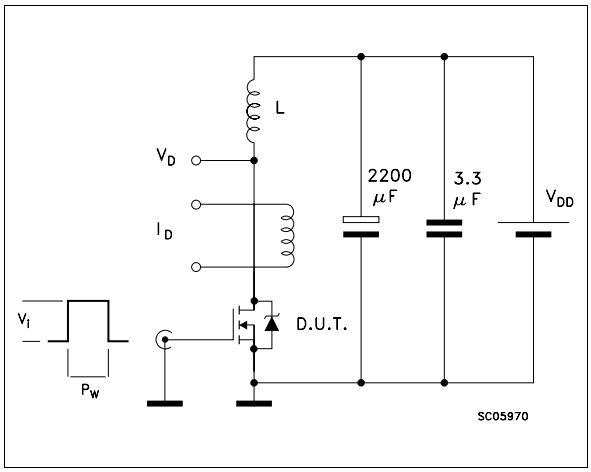


Fig. 2: Unclamped Inductive Waveform

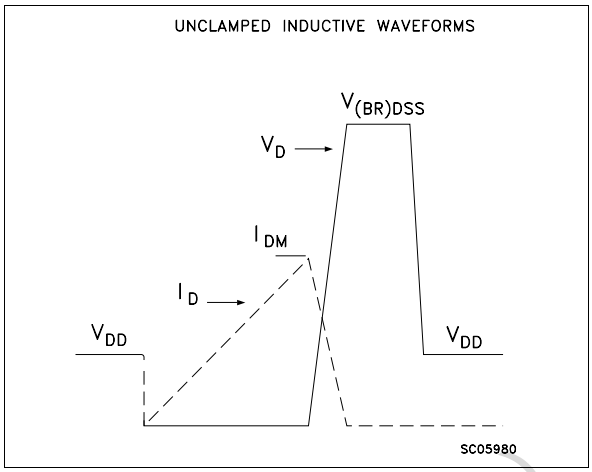


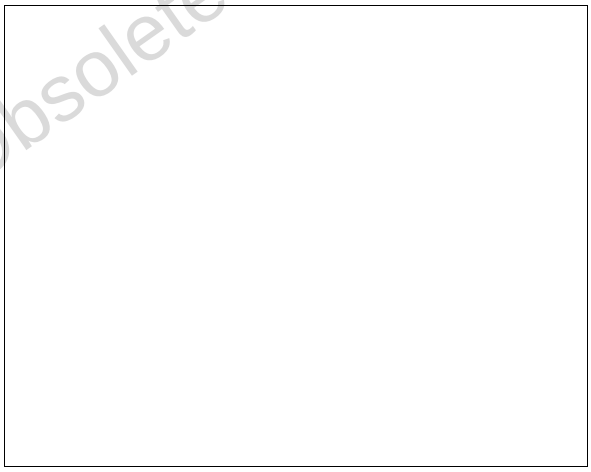
Fig. 3: Switching Times Test Circuits For Resistive Load



Fig. 4: Gate Charge test Circuit



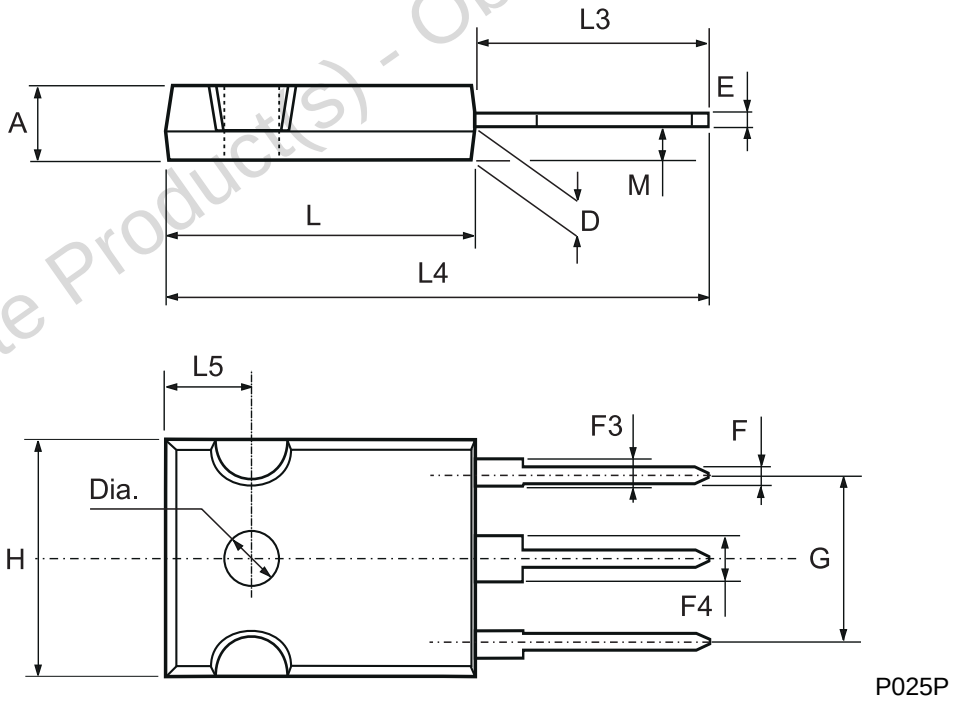
Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



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TO-247 MECHANICAL DATA

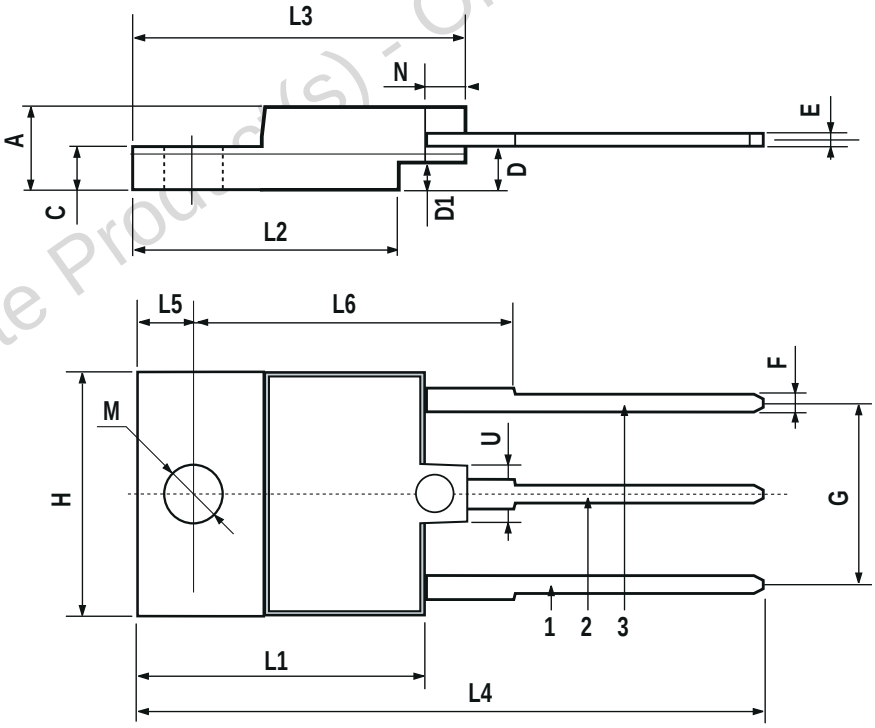
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		5.3	0.185		0.209
D	2.2		2.6	0.087		0.102
E	0.4		0.8	0.016		0.031
F	1		1.4	0.039		0.055
F3	2		2.4	0.079		0.094
F4	3		3.4	0.118		0.134
G		10.9			0.429	
H	15.3		15.9	0.602		0.626
L	19.7		20.3	0.776		0.779
L3	14.2		14.8	0.559	0.413	0.582
L4		34.6			1.362	
L5		5.5			0.217	
M	2		3	0.079		0.118
Dia	3.55		3.65	0.140		0.144



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ISOWATT218 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	5.35		5.65	0.210		0.222
C	3.3		3.8	0.130		0.149
D	2.9		3.1	0.114		0.122
D1	1.88		2.08	0.074		0.081
E	0.75		1	0.029		0.039
F	1.05		1.25	0.041		0.049
G	10.8		11.2	0.425		0.441
H	15.8		16.2	0.622		0.637
L1	20.8		21.2	0.818		0.834
L2	19.1		19.9	0.752		0.783
L3	22.8		23.6	0.897		0.929
L4	40.5		42.5	1.594		1.673
L5	4.85		5.25	0.190		0.206
L6	20.25		20.75	0.797		0.817
M	3.5		3.7	0.137		0.145
N	2.1		2.3	0.082		0.090
U		4.6			0.181	



P025C

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